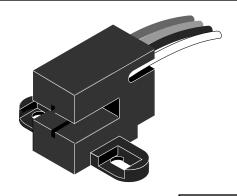


NOTES:

- 1. Dimensions are in inches (mm)
- 2. Tolerance of ± .010 (.25) on all non nominal dimensions unless otherwise specified.
- 3. Wire gauge: 28 AWG



SCHEMATIC

RED

WHITE

DARK GREEN

FEATURES

- No contact switching
- 2.41 mm wide slot
- · Slot horizontal to mounting surface
- Mounting tabs
- Transistor Output
- Wire leads for remote connection 10" (254mm)
- Opaque black plastic housing
- 0.010 (0.25) aperture width

NOTES (Applies to Max Ratings and Characteristics Tables.)

- 1. Derate power dissipation linearly 1.67 mW/°C above 25°C.
- 2. RMA flux is recommended.
- 3. Methanol or isopropyl alcohols are recommended as cleaning agents.
- 4. Soldering iron 1/16" (1.6mm) minimum from housing.

Parameter	Symbol	Rating	Units
Operating Temperature	T _{OPR}	-40 to +85	°C
Storage Temperature	T _{STG}	-40 to +85	°C
Lead Soldering Temperature (Iron)(2,3,4)	T _{SOL-I}	240 for 5 sec	°C
EMITTER			
Continuous Forward Current	I _F	50	mA
Reverse Voltage	V _R	5	V
Power Dissipation ⁽¹⁾	P _D	100	mW
SENSOR			
Collector-Emitter Voltage	V _{CEO}	30	V
Emitter-Collector Voltage	V _{ECO}	4.5	V
Power Dissipation(1)	P _D	100	mW

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ELECTRICAL / OPTICAL CHARACTERISTICS (T _A = 25°C)									
PARAMETER	TEST CONDITIONS	SYMBOL	MIN	TYP	MAX	UNITS			
EMITTER									
Forward Voltage	$I_F = 20 \text{ mA}$	V_{F}	_	_	1.7	V			
Reverse Current	$V_R = 5 V$	I_R	_	_	100	μΑ			
Peak Emission Wavelength	$I_F = 20 \text{ mA}$	λ_{PE}	_	940	_	nm			
SENSOR									
Collector-Emitter Breakdown	$I_C = 1 \text{ mA}$	BV_CEO	30	_	_	V			
Emitter-Collector Breakdown	I _E = 0.1 mA	BV _{ECO}	5	_	_	V			
Dark Current	V _{CE} = 10 V, I _F = 0 mA	I _D	_	_	100	nA			
COUPLED									
Collector Current	$I_F = 20 \text{ mA}, V_{CE} = 10 \text{ V}$	$I_{C(ON)}$	0.5	_	_	mA			
Collector Emitter	$I_F = 20 \text{ mA}, I_C = 0.4 \text{ mA}$	V _{CE (SAT)}	_	_	0.4	V			
Saturation Voltage									
Rise Time	V_{CE} = 5 V, R_L = 100 Ω	t _r	_	8	_	μs			
Fall Time	$I_{C(ON)} = 5 \text{ mA}$	t_f	_	50	_	μs			

TYPICAL PERFORMANCE CURVES

Fig. 1 Forward Voltage vs. Ambient Temperature

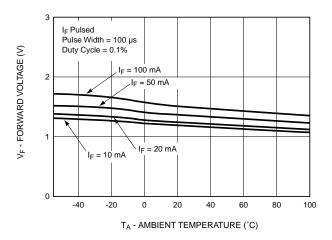


Fig. 3 Collector Emitter Dark Current (Normalized) vs. Ambient Temperature

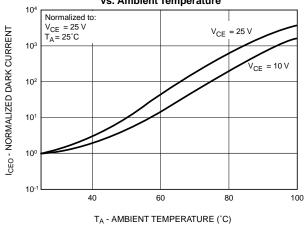


Fig. 2 Forward Current Vs. Forward Voltage

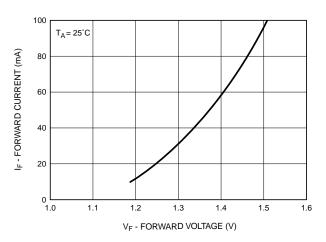
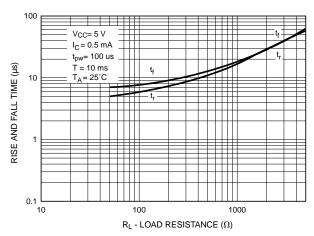


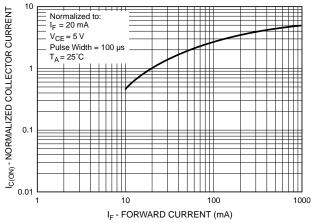
Fig. 4 Rise and Fall Time vs. Load Resistance



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Fig. 5 Normalized Collector Current vs. Forward Current



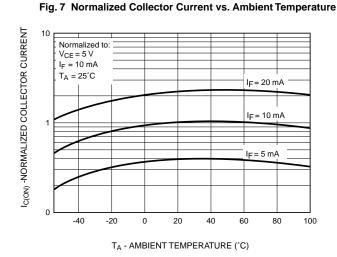


Fig. 6 Collector Current vs. Collector to Emitter Voltage

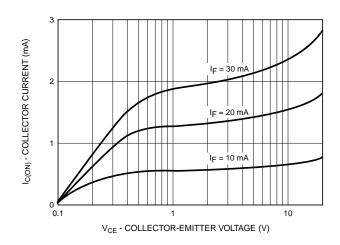


Fig. 8 Normalized Collector Current vs. Shield Distance

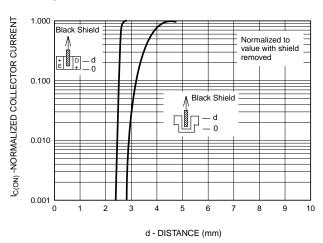
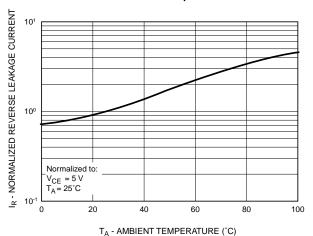


Fig. 9 Normalized Reverse Leakage Current vs. Ambient Temperature



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